NPN SILICON RF POWER TRANSISTOR

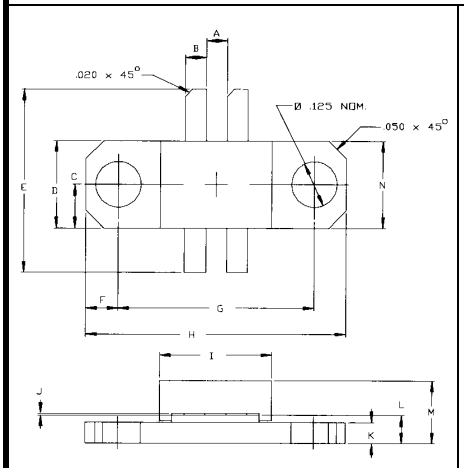
DESCRIPTION:

The **TPV5051-1** is Designed for AB Push Pull, Common Emitter from 470 to 860 MHz Applications.

MAXIMUM RATINGS

I_C	2.6 A (EACH SIDE)
V_{CE}	25 V
P_{DISS}	65 W @ T_C = 25 °C (TOTAL)
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.5 °C/W

PACKAGE STYLE BMA 2A



1 = EMITTER/FLANGE
3 = BASE 2 = CHAMFERED 45°
LEADS = COLLECTOR

	MIN: (In/mm)	MAX: (In/mm)
A	.060/1.52	.060/1.52
B	.055/1.40	.065/1.65
C	.124/3.15	.124/3.15
D	.234/6.17	.253/6.34
E	.635/16.13	.665/16.89
F	.092/.234	.092/.234
G	.555/14.10	.565/14.35
H	.739/18.77	.749/19.02
I	.315/8.00	.327/8.31
J	.002/0.05	.006/0.15
K	.055/1.40	.065/1.65
L	.075/1.91	.095/2.41
M		.190/4.83
N	.245/6.22	.257/6.53

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 40 mA	25			V
BV_{CBO}	I_C = 20 mA	45			V
BV_{EBO}	I_E = 6.0 mA	4.0			V
h_{FE}	V_{CE} = 20 V I_C = 800 mA	10			---
C_{ob}	V_{CB} = 28 V f = 1.0 MHz (EACH SIDE)			40	pF
P_G	V_{CE} = 28 V P_{out} = 50 W Iq = 2X100 mA	6.5			dB
η_C	f = 860 MHz	45			%

Specifications are subject to change without notice.